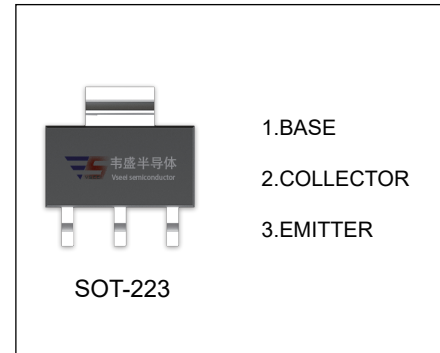


CZT5401 TRANSISTOR (PNP)

FEATURES

- High Voltage
- High Voltage Amplifier Application



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-600	mA
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.1\text{mA}, I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.01\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$			-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-1\text{mA}$	50			
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$	100		300	
	$h_{FE(3)}$	$V_{CE}=-5\text{V}, I_C=-50\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-0.2	V
		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10\text{mA}, I_B=-1\text{mA}$			-1	V
		$I_C=-50\text{mA}, I_B=-5\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	100		300	MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			6	pF